

On the temperature dependence of 2D "metallic" conductivity in Si inversion layers at intermediate temperatures

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We show that the recent experimental claim of Pudarov et al. [Phys. Rev. Lett. 91, 126403 (2003)] of observing "interaction effects in the conductivity of Si inversion layers at intermediate temperatures" is incorrect and misleading. In particular, the temperature dependent conductivity, in contrast to the resistivity (which is what is shown in the paper), does not have a linear temperature regime, rendering the extraction of the slope $d\sigma/dT$ completely arbitrary. We also show that, at least for higher densities, the standard semiclassical transport theory, which includes realistic disorder effects such as scattering by screened charged impurity and surface roughness, gives essentially quantitative agreement with the experimental data.

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In a recent Letter [1], here after referred to as I, Pudarov et al. have presented experimental results on the temperature dependent resistivity $\rho(T)$ of Si inversion layers comparing the data to the so-called interaction theory [2] of Zala et al. Although claims of "rigorous experimental test" and "excellent agreement" are made rather uncritically in I, the purpose of the current Comment is to point out the misleading and essentially incorrect nature of the main claims in I. In particular, we point out that (1) the comparison to the theory of ref. [2] carried out in I is inappropriate and arbitrary; and (2) the well-established semiclassical Boltzmann transport theory [3,6] for Si inversion layers using screened charged impurity scattering and interface roughness scattering provides quantitative agreement with much of the higher density data ($n \gtrsim 5 \times 10^{11} \text{ cm}^{-2}$) presented in I with the agreement becoming qualitative at lower densities.

The interaction theory [2], with which Pudarov et al. compare their data, predicts a linear T -dependence of the conductivity $\sigma(T) = \sigma_0 + F \frac{T}{T_F}$ in the intermediate temperature ballistic regime where σ_0 is the $T = 0$ "Drude" conductivity and T_F the Fermi temperature. The slope $F = F(r_s)$, which depends on the dimensionless $r_s \propto (n^{-1/2})$ parameter, cannot be calculated within the theory and is predicted to change its sign at high density (which has not yet been observed experimentally). The absolute necessary condition (but, by no means sufficient) for verifying the theory of ref. [2] is obviously an observation of a linear temperature dependent conductivity over a reasonable temperature range. This is particularly so in view of the fact that the interaction theory [2] can only predict the qualitative leading order temperature dependence, but not the quantitative magnitude of the slope F for the $\sigma(T)$ curves. A rudimentary analysis of the data presented in I clearly shows that $\sigma(T)$ results of I are nonlinear, and thus do not satisfy the minimal necessary condition needed for a comparison with the interaction theory. The authors of I have taken the misleading step of presenting their data for the resistivity

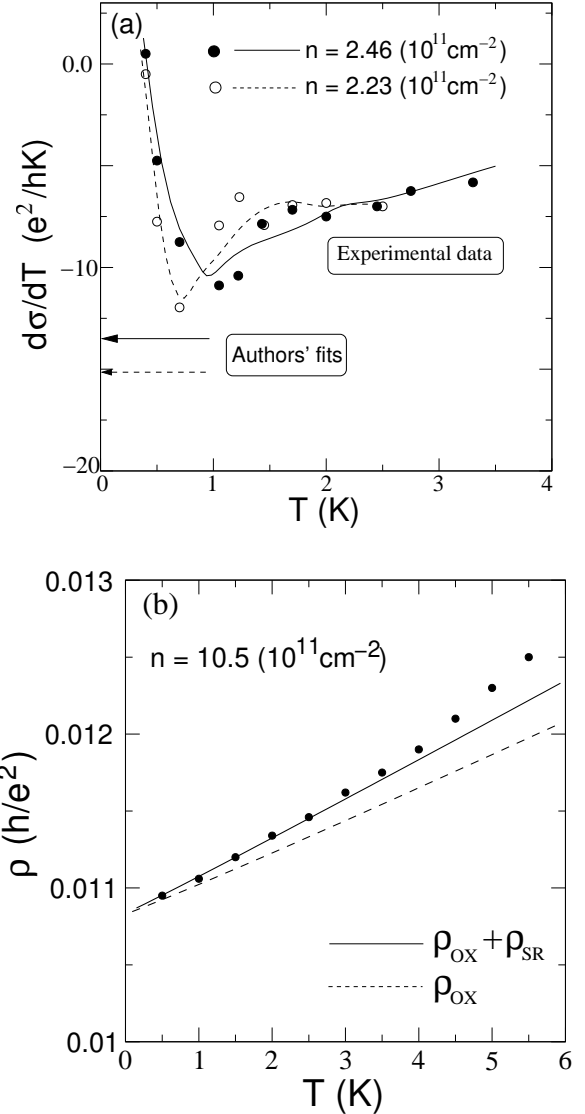


FIG. 1. (a) $d\sigma/dT$ using an interpolation scheme (lines) for the data of I with the slope used in I shown as arrows. Dots in (a) represent the average slope at the data points without any interpolation. (b) The calculated resistivity including screened interface charged impurity and surface roughness scattering. Dots indicate experimental data from I.

$\rho(T)$, rather than the conductivity $\sigma(T) = [\rho(T)]^{-1}$. The $\rho(T)$ data in I supercially appear relatively more linear than the corresponding $\sigma(T)$ results, and quite trivially even a linear $\rho(T)$ is not equivalent to a linear $\sigma(T)$ unless the temperature correction is small, which is manifestly not the case in I (i.e. the temperature dependence is not weak except at the highest densities where the Boltzmann theory gives quantitatively accurate results).

We show in Fig. 1(a) our best estimate for $d\rho/dT$ extracted numerically for the data of I, and it is obvious that a linear-T approximation to $\rho(T)$, i.e. a constant $d\rho/dT$ over any reasonable range of temperature, simply does not apply anywhere in the data making the whole exercise of the comparison to the interaction theory completely arbitrary. In Fig. 1(b) we show an essentially parameter-free quantitative comparison between the high-density data in I and the standard semiclassical Boltzmann transport theory including realistic effects of screened interface charged impurity and surface roughness scattering. This quantitative agreement remains good down to about $5 \times 10^{11} \text{ cm}^{-2}$ below which the experimental $\rho(T)$ shows stronger nonlinear temperature dependence at higher ($> 3\text{ K}$) temperature, but the intermediate temperature ($< 1\text{ K}$) slope $d\rho/dT$ continues to agree well with the prediction of the realistic Boltzmann theory. The quantitative agreement between the Boltzmann theory and the data of I can be further improved (down to lower densities) by including scattering by bulk charged impurity centers and by adjusting the carrier density and/or carrier effective mass (as well as an improved screening function including effects of scattering and local field correction).

We conclude by pointing out that the $\rho(T)$ data presented in I shows smooth evolution from high to low density with only the quantitative temperature dependence becoming stronger in a continuous manner with decreasing carrier density. This indicates that the temperature dependent disorder (e.g. screened Coulomb scattering) is playing an important role since at high and intermediate densities one gets quantitative agreement between the realistic Boltzmann theory and the experimental $\rho(T)$ | qualitatively, lowering density is weakening screening leading to stronger temperature dependent disorder and consequently larger resistivity.

[6] S. Das Sarma and E. H. Hwang, Phys. Rev. Lett. 83, 164 (1999); cond-mat/0302047.

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- [1] V. Pudalov et al., Phys. Rev. Lett. 91, 126403 (2003).
 - [2] G. Zala et al., Phys. Rev. B 64, 214204 (2001).
 - [3] F. Stern, Phys. Rev. Lett. 44, 1469 (1980).
 - [4] T. Ando et al., Rev. Mod. Phys. 54 437, (1982).
 - [5] A. G. Gold and V. T. Dolgoplov, Phys. Rev. B 33, 1076 (1986); S. Das Sarma, Phys. Rev. B 33, 5401 (1986).